



# 7<sup>th</sup> IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

March 7 – 10, 2023 / COEX Seoul, Korea

6F. DRAM and Flash	
Session Date:	March 8(Wed.), 2023
Session Time:	10:55-12:30
Session Room:	Room F (#317)
Session Chair:	Prof. Jiyong Woo (Kyungpook National University) Prof. Jongwook Jeon (Konkuk University)

**[6F-1] [Invited] 10:55-11:20**

## DRAM Technology Trends and Future Perspective

Sangyeon Han, Junsoo Kim, Suklae Kim, Sung Ho Jang, Seokhan Park, Jin-Woo Han and Jemin Park

*Samsung Electronics Co., Ltd.*

**[6F-2] 11:20-11:35**

## Dual-Float-Gate Capacitor for Low-Voltage Multi-Level Nonvolatile Memory with Enhanced Retention

Haixia Li<sup>1</sup>, Hongxu Liao<sup>1</sup>, Baotong Zhang<sup>1</sup>, Ran Bi<sup>1</sup>, Ru Huang<sup>1,2</sup> and Ming Li<sup>1,2</sup>

<sup>1</sup>Peking University, <sup>2</sup>Beijing Advanced Innovation Center for Integrated Circuits

**[6F-3] 11:35-11:50**

## Quantitative Analysis of Tunnel Oxide Nitrogen Concentration in 3D NAND Using Low Acceleration Voltage, Low Current and Low Temperature STEM-EELS

Jun-Young Lee, Woo-Young Jung, Jongkyu Cho, Jangwon Oh, Jonghun Kim and Minki Choi

*SK hynix Inc.*

**[6F-4] 11:50-12:05**

## Temperature-Induced Instability of Retention Characteristics in 3-D NAND Flash Memory

Ukju An, Gilsang Yoon, Donghyun Go, Jounghun Park, Donghwi Kim, Jongwoo Kim and Jeong-Soo Lee

*Pohang University of Science and Technology*

**[6F-5] [Invited] 12:05-12:30**

## 2-Transistor (2T) Dynamic Random-Access Memory towards Processing-in-Memory Featuring Bitwise Dual-Mode Operations

Jong-Ho Bae<sup>1</sup>, Yong Shim<sup>2</sup> and Seongjae Cho<sup>3</sup>

<sup>1</sup>Kookmin University, <sup>2</sup>Chung-Ang University, <sup>3</sup>Gachon University